General Description

The WSP4807 is the highest performance trench P-ch MOSFET with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The WSP4807 meet the RoHS and Green Product requirement with full function reliability approved.

Product Summery

BVDSS	RDSON	ID
-30V	33mΩ	-6.5A

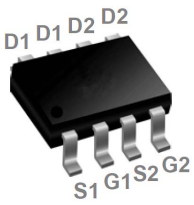
Applications

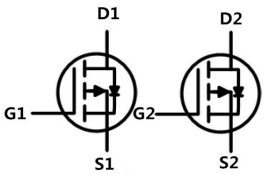
- Power Management in Notebook Computer, Portable Equipment and Battery Powered Systems.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Green Device Available

SOP-8 Pin Configuration





Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current, $-V_{GS}$ @ -10V[1]	-6.5	A
I_D@T_C=100℃	Continuous Drain Current, $-V_{GS}$ @ -10V[1]	-5.3	A
I_{DM}	Pulsed Drain Current[2]	-20	A
P_D@T_C=25℃	Total Power Dissipation[3]	1.5	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	---	85	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	---	36	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250uA	-30	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BVDSS Temperature Coefficient	Reference to 25℃ , I_D=-1mA	---	-0.	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=-10V , I_D=-3A	---	33	46	mΩ
		V_{GS}=-4.5V , I_D=-1.5A	---	53	72	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =-250uA	-1.0	-		V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	4.	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-24V , V_{GS}=0V , T_J=25℃	---	-	-1	uA
		V_{DS}=-24V , V_{GS}=0V , T_J=55℃	---	-	-5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	-	±100	nA
gfs	orward Transconductance	V_{DS}=-5V , I_D=-3A	---	5		S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	24	48	Ω
Q_g	Total Gate Charge (-4.5V)	V_{DS}=-20V , V_{GS}=-4.5V , I_D=-5A	---	6.2	---	nC
Q_{gs}	Gate-Source Charge		---	2.5	---	
Q_{gd}	Gate-Drain Charge		---	3.3	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=-15V , V_{GS}=-10V , R_G=3.3Ω I_D=-1A	---	9.2	---	ns
T_r	Rise Time		---	16.5	---	
$T_{d(off)}$	Turn-Off Delay Time		---	21.3	---	
T_f	Fall Time		---	21.5	---	
C_{iss}	Input Capacitance	V_{DS}=-15V , V_{GS}=0V , f=1MHz	---	640	---	pF
C_{oss}	Output Capacitance		---	270	---	
C_{rss}	Reverse Transfer Capacitance		---	103	---	

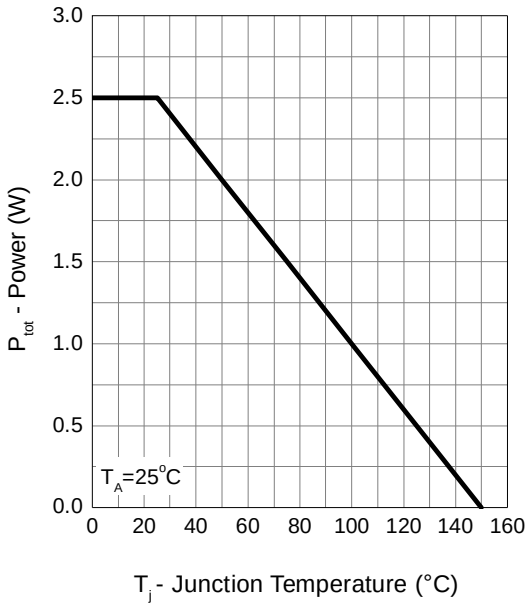
Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,4]	V_G=V_D=0V , Force Current	---	---	-6.5	A
I_{SM}	Pulsed Source Current[2,4]		---	-	-12	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=-1A , T_J=25℃	---	-	-1.2	V

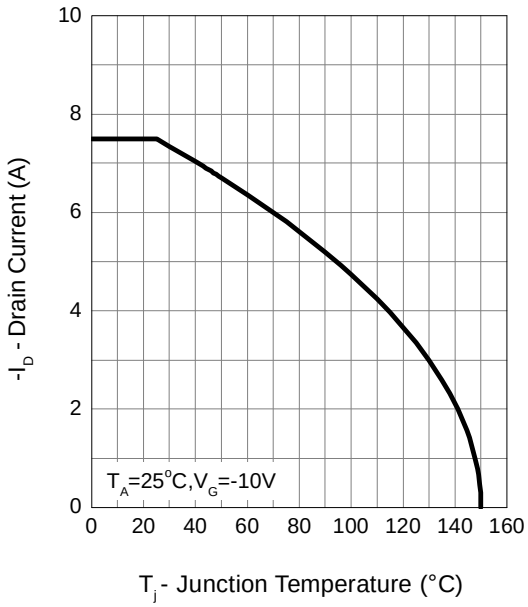
Note :
1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper,t<10sec.
2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3.The power dissipation is limited by 150℃ junction temperature
4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Operating Characteristics

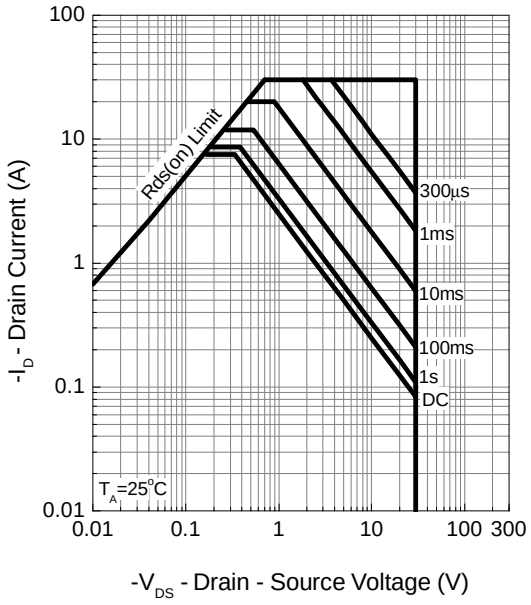
Power Dissipation



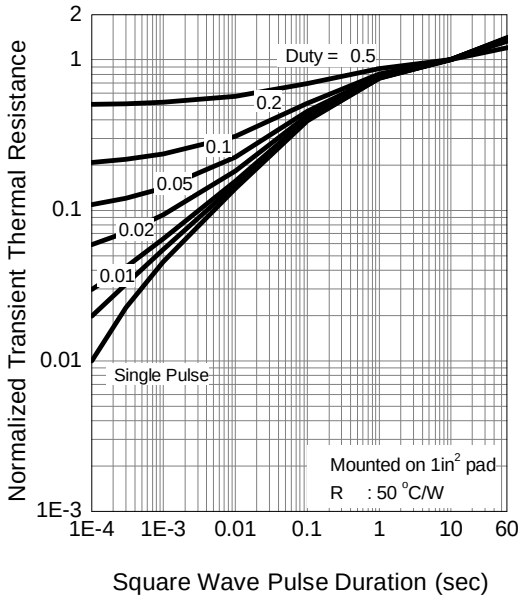
Drain Current



Safe Operation Area

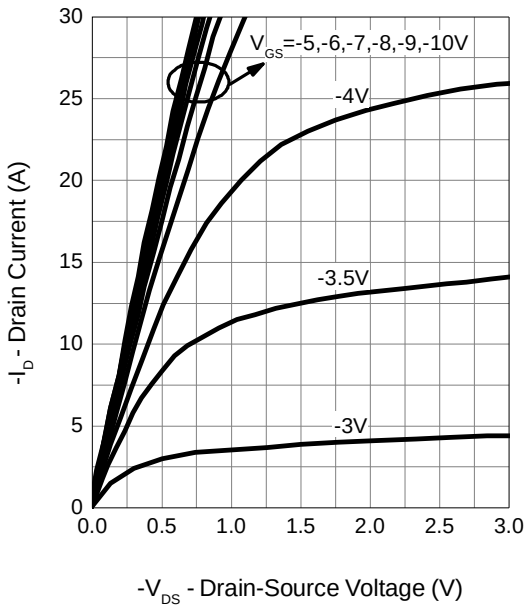


Thermal Transient Impedance

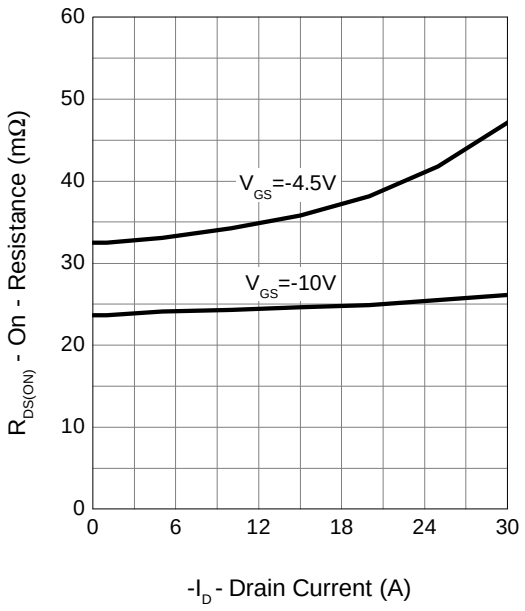


Typical Operating Characteristics (Cont.)

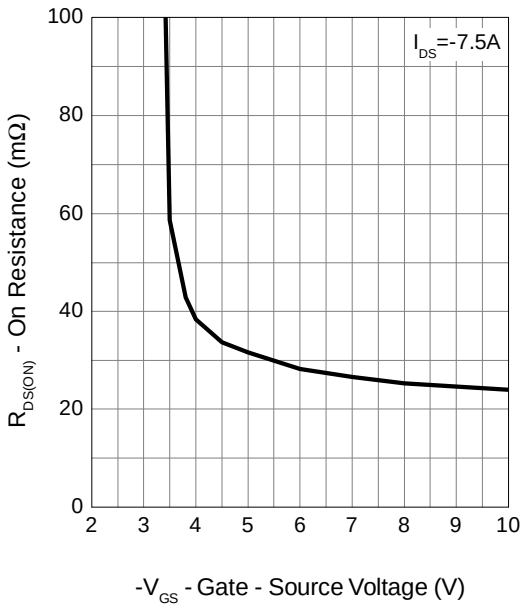
Output Characteristics



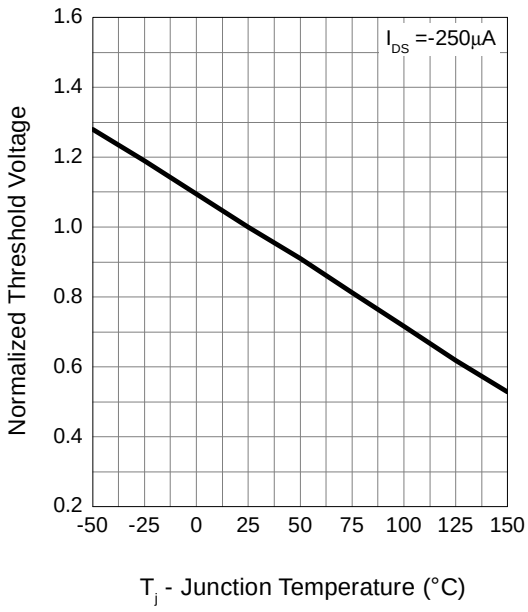
Drain-Source On Resistance



Gate-Source On Resistance

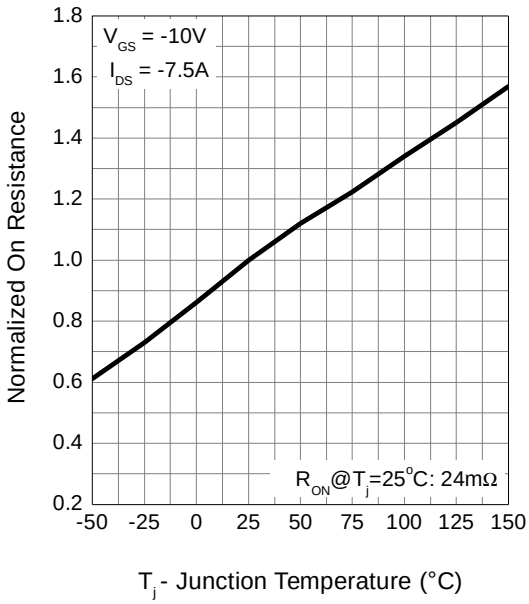


Gate Threshold Voltage

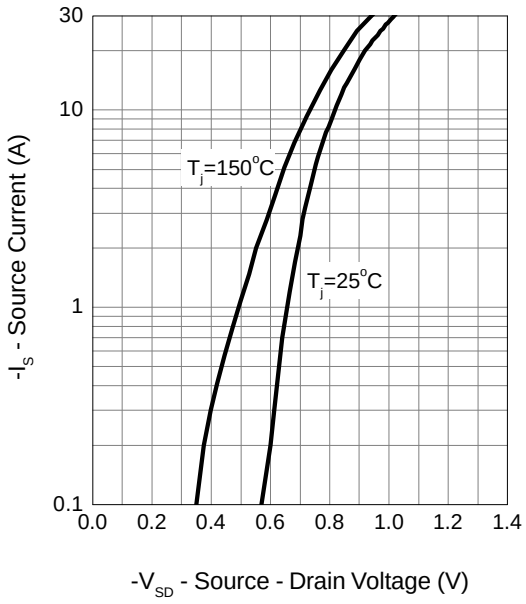


Typical Operating Characteristics (Cont.)

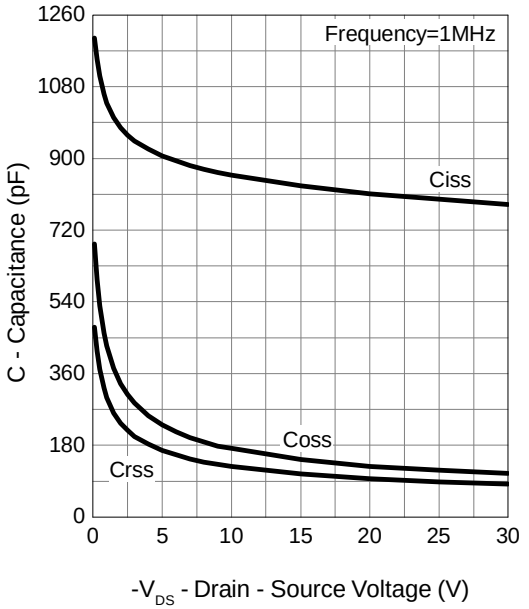
Drain-Source On Resistance



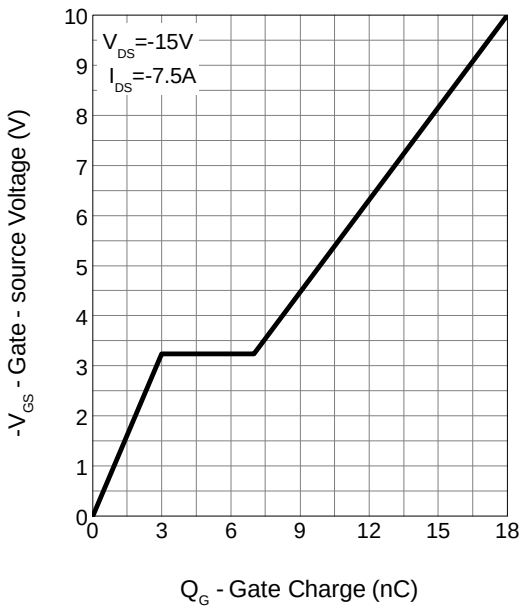
Source-Drain Diode Forward



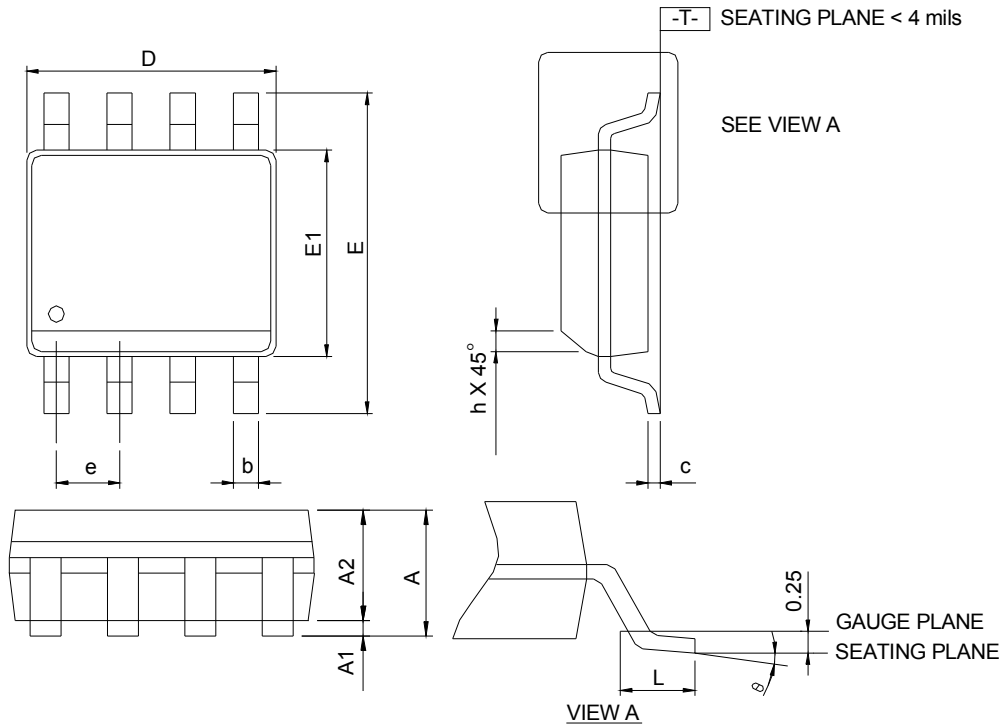
Capacitance



Gate Charge



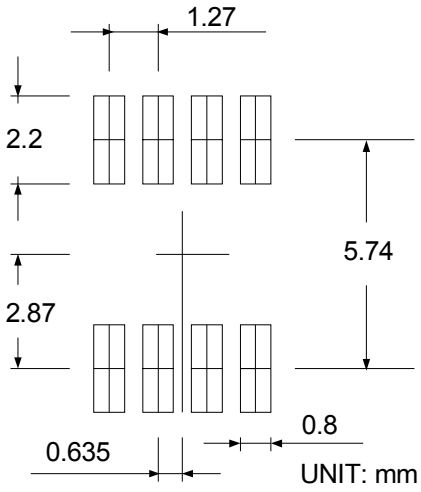
Package Information SOP-8



SYMBOL	SOP-8			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A		1.75		0.069
A1	0.10	0.25	0.004	0.010
A2	1.25		0.049	
b	0.31	0.51	0.012	0.020
c	0.17	0.25	0.007	0.010
D	4.80	5.00	0.189	0.197
E	5.80	6.20	0.228	0.244
E1	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
h	0.25	0.50	0.010	0.020
L	0.40	1.27	0.016	0.050
θ	0°	8°	0°	8°

Note: 1. Follow JEDEC MS-012 AA.
2. Dimension “D” does not include mold flash, protrusions or gate burrs. Mold flash, protrusion or gate burrs shall not exceed 6 mil per side.
3. Dimension “E” does not include inter-lead flash or protrusions. Inter-lead flash and protrusions shall not exceed 10 mil per side.

RECOMMENDED LAND PATTERN



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